

# STB80NF55-08T4 STP80NF55-08, STW80NF55-08

N-channel 55 V, 0.0065 Ω, 80 A, TO-220, D<sup>2</sup>PAK, TO-247 STripFET™ Power MOSFET

### **Features**

Туре	V <sub>DSS</sub>	R <sub>DS(on)</sub> max	I <sub>D</sub>
STB80NF55-08T4	55 V	< 0.008 Ω	80 A
STP80NF55-08	55 V	< 0.008 Ω	80 A
STW80NF55-08	55 V	< 0.008 Ω	80 A

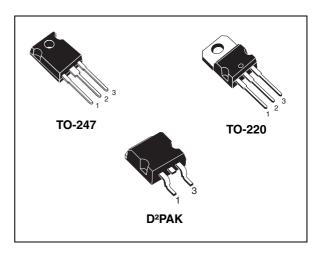
■ Standard threshold drive

### Application

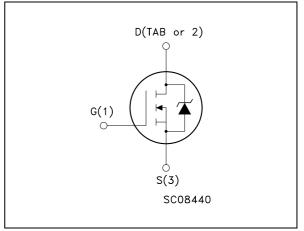
Switching applications

### Description

This Power MOSFET is the latest development of STMicroelectronics unique "single feature size" strip-based process. The resulting transistor shows extremely high packing density for low onresistance, rugged avalance characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.



#### Figure 1. Internal schematic diagram



### Table 1. Device summary

Order codes	Marking	Package	Packaging
STB80NF55-08T4	B80NF55-08	D <sup>2</sup> PAK	Tape and reel
STP80NF55-08	P80NF55-08	TO-220	Tube
STW80NF55-08	W80NF55-08	TO-247	Tube

April 2009
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## 1 Electrical ratings

Table 2.	Absolute	maximum	ratings
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Symbol	Parameter	Value	Unit
V <sub>DS</sub>	Drain-source voltage ( $V_{GS} = 0$ )	55	V
V <sub>GS</sub>	Gate- source voltage	±20	V
I <sub>D</sub> <sup>(1)</sup>	Drain current (continuos) at $T_C = 25 \ ^{\circ}C$	80	А
I <sub>D</sub> <sup>(1)</sup>	Drain current (continuos) at T <sub>C</sub> = 100 °C	80	А
I <sub>DM</sub> <sup>(2)</sup>	Drain current (pulsed)	320	А
P <sub>TOT</sub>	Total dissipation at $T_C = 25 \ ^{\circ}C$	300	W
	Derating factor	2	W/°C
T <sub>j</sub> T <sub>stg</sub>	Operating junction temperature Storage temperature	-55 to 175	°C

1. Current limited package

2. Pulse width limited by safe operating area

Symbol	Parameter	Value			Unit
Symbol	Falameter	D <sup>2</sup> PAK	TO-220	TO-247	Unit
R <sub>thj-case</sub>	Thermal resistance junction-case max		0.5		°C/W
R <sub>thj-amb</sub>	Thermal resistance junction-ambient max	35 <sup>(1)</sup>	62.5	50	°C/W
Τ <sub>Ι</sub>	Maximum lead temperature for soldering purpose	300			°C

1. When mounted on 1 inch<sup>2</sup> FR-4 board, 2 oz Cu

 Table 4.
 Avalanche characteristics

Symbol	Parameter	Max value	Unit
I <sub>AR</sub>	Avalanche current, repetitive or not-repetitive (pulse width limited by T <sub>j</sub> max)	40	A
E <sub>AS</sub>	Single pulse avalanche energy (starting $T_j = 25 \text{ °C}, I_D = I_{AR}, V_{DD} = 30 \text{ V}$ )	1000	mJ



### 2 Electrical characteristics

(T<sub>CASE</sub> = 25 °C unless otherwise specified)

	On/on states					
Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
V <sub>(BR)DSS</sub>	Drain-source breakdown voltage	$I_D = 250 \ \mu A, \ V_{GS} = 0$	55			V
I <sub>DSS</sub>	Zero gate voltage drain current (V <sub>GS</sub> = 0)	$V_{DS}$ = max rating $V_{DS}$ = max rating@125 °C			1 10	μΑ μΑ
I <sub>GSS</sub>	Gate body leakage current (V <sub>DS</sub> = 0)	$V_{GS} = \pm 20 V$			±100	nA
V <sub>GS(th)</sub>	Gate threshold voltage	$V_{DS} = V_{GS}, \ I_D = 250 \ \mu A$	2	3	4	V
R <sub>DS(on)</sub>	Static drain-source on resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 40 A		0.0065	0.008	Ω

#### Table 5. On/off states

#### Table 6. Dynamic

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
g <sub>fs</sub> <sup>(1)</sup>	Forward transconductance	$V_{DS}$ =15 V , $I_{D}$ = 18 A		40		S
C <sub>iss</sub> C <sub>oss</sub> C <sub>rss</sub>	Input capacitance Output capacitance Reverse transfer capacitance	V <sub>DS</sub> = 25 V, f = 1 MHz, V <sub>GS</sub> = 0		3740 830 265		pF pF pF
Q <sub>g</sub> Q <sub>gs</sub> Q <sub>gd</sub>	Total gate charge Gate-source charge Gate-drain charge	$V_{DD}$ = 27 V, $I_D$ = 80 A $V_{GS}$ =10 V (see Figure 14)		112 20 40	155	nC nC nC

1. Pulsed: pulse duration=300 µs, duty cycle 1.5%

Table 7.	Switching	times
	Owncoming	unico

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
t <sub>d(on)</sub> t <sub>r</sub> t <sub>d(off)</sub> t <sub>f</sub>	Turn-on delay time Rise time Turn-off-delay time Fall time	$V_{DD} = 27 \text{ V}, I_D = 40 \text{ A}$ $R_G = 4.7 \Omega V_{GS} = 10 \text{ V}$ (see Figure 13)		20 110 75 35		ns ns ns ns



Symbol	Parameter	Test conditions	Min	Тур.	Max	Unit
I <sub>SD</sub>	Source-drain current				80	А
I <sub>SDM</sub> <sup>(1)</sup>	Source-drain current (pulsed)				320	А
$V_{SD}$	Forward on voltage	$I_{SD} = 80 \text{ A}, V_{GS} = 0$			1.5	V
t <sub>rr</sub> <sup>(2)</sup> Q <sub>rr</sub> I <sub>RRM</sub>	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD} = 80 \text{ A}, V_{DD} = 25 \text{ V}$ di/dt=100 A/ $\mu$ s, $T_j = 150 \text{ °C}$ (see Figure 18)		80 230 5.7		ns nC A

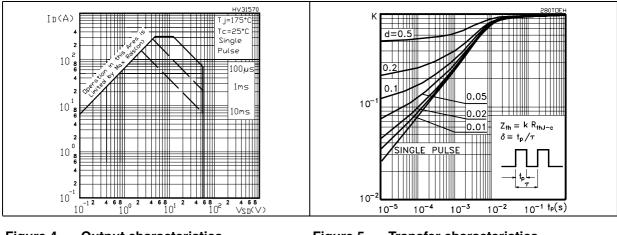
 Table 8.
 Source drain diode

1. Pulse width limited by safe operating area

2. Pulsed: pulse duration =  $300\mu s$ , duty cycle 1.5%

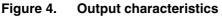


### 2.1 Electrical characteristics (curves)



#### Figure 2. Safe operating area

Figure 3. Thermal impedance





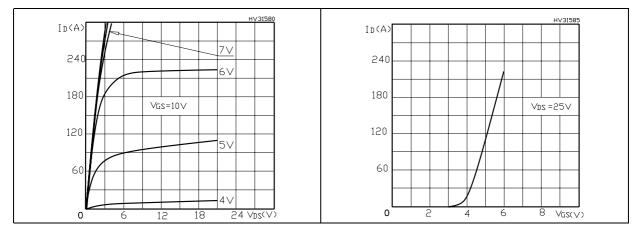
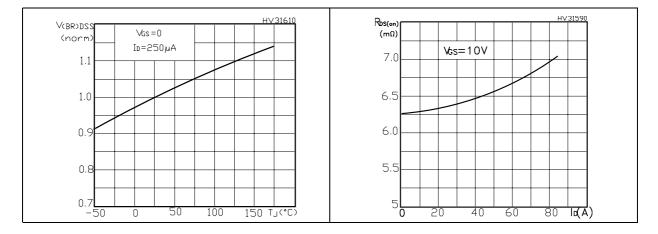


Figure 6. Normalized BV<sub>DSS</sub> vs temperature Figure 7. Static drain-source on resistance





#### Gate charge vs gate-source voltage Figure 9. Figure 8. **Capacitance variations**

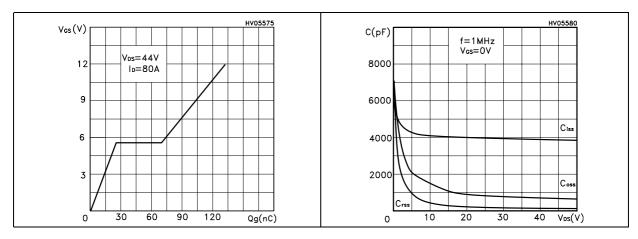


Figure 10. Normalized gate threshold voltage Figure 11. Normalized on resistance vs vs temperature

temperature

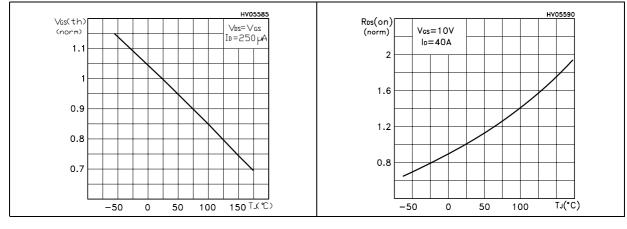


Figure 12. Source-drain diode forward characteristics

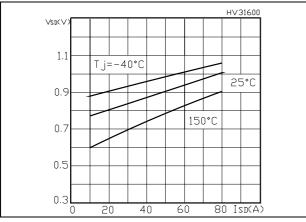


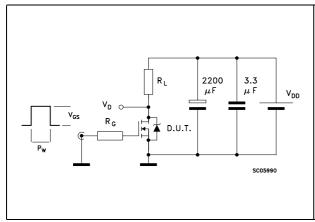


Figure 14. Gate charge test circuit

circuit

#### 3 **Test circuits**

Figure 13. Switching times test circuit for resistive load



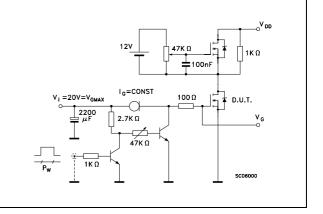
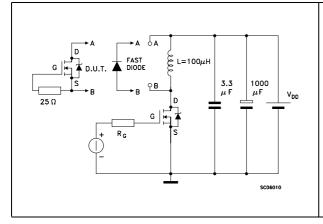
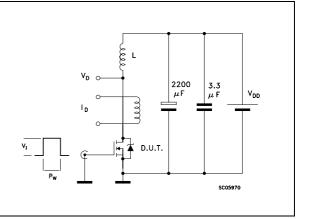


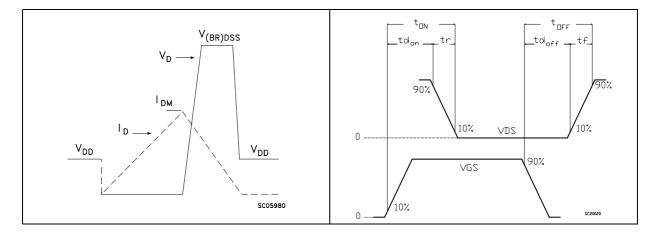
Figure 16. Unclamped inductive load test Figure 15. Test circuit for inductive load switching and diode recovery times











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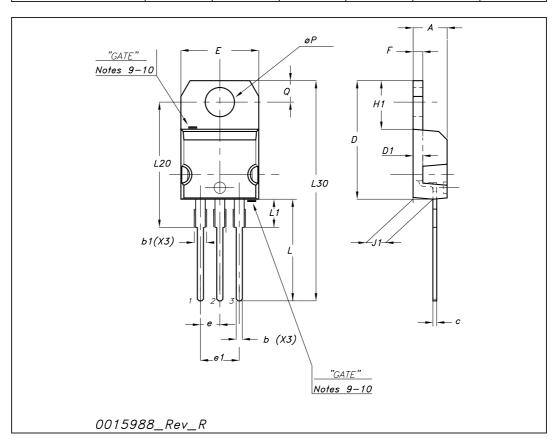
### 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.



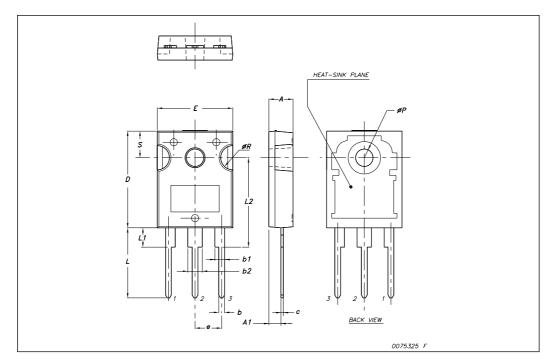
Dim		mm			inch			
Dim	Min	Тур	Мах	Min	Тур	Max		
А	4.40		4.60	0.173		0.181		
b	0.61		0.88	0.024		0.034		
b1	1.14		1.70	0.044		0.066		
С	0.48		0.70	0.019		0.027		
D	15.25		15.75	0.6		0.62		
D1		1.27			0.050			
E	10		10.40	0.393		0.409		
е	2.40		2.70	0.094		0.106		
e1	4.95		5.15	0.194		0.202		
F	1.23		1.32	0.048		0.051		
H1	6.20		6.60	0.244		0.256		
J1	2.40		2.72	0.094		0.107		
L	13		14	0.511		0.551		
L1	3.50		3.93	0.137		0.154		
L20		16.40			0.645			
L30		28.90			1.137			
ØP	3.75	İ	3.85	0.147		0.151		
Q	2.65	İ	2.95	0.104		0.116		







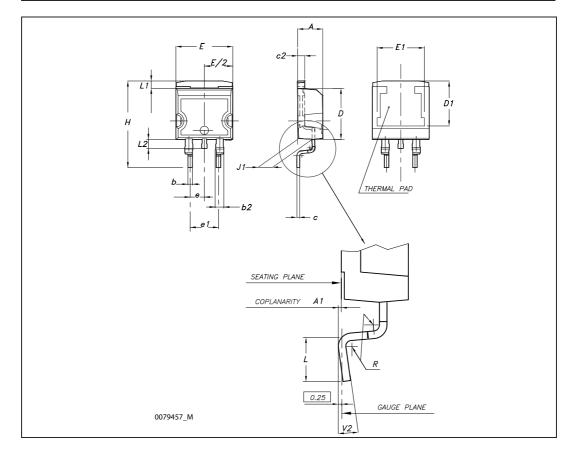
	TO-247 Mechanical data				
Dim.	mm.				
	Min.	Тур	Max.		
Α	4.85		5.15		
A1	2.20		2.60		
b	1.0		1.40		
b1	2.0		2.40		
b2	3.0		3.40		
С	0.40		0.80		
D	19.85		20.15		
E	15.45		15.75		
е		5.45			
L	14.20		14.80		
L1	3.70		4.30		
L2		18.50			
øР	3.55		3.65		
øR	4.50		5.50		
S		5.50			





D <sup>2</sup> PAK (TO-263) mechanical data

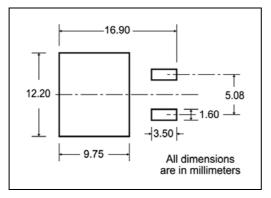
Dim		mm			inch			
	Min	Тур	Max	Min	Тур	Max		
A	4.40		4.60	0.173		0.181		
A1	0.03		0.23	0.001		0.009		
b	0.70		0.93	0.027		0.037		
b2	1.14		1.70	0.045		0.067		
С	0.45		0.60	0.017		0.024		
c2	1.23		1.36	0.048		0.053		
D	8.95		9.35	0.352		0.368		
D1	7.50			0.295				
E	10		10.40	0.394		0.409		
E1	8.50			0.334				
е		2.54			0.1			
e1	4.88		5.28	0.192		0.208		
Н	15		15.85	0.590		0.624		
J1	2.49		2.69	0.099		0.106		
L	2.29		2.79	0.090		0.110		
L1	1.27		1.40	0.05		0.055		
L2	1.30		1.75	0.051		0.069		
R		0.4			0.016			
V2	0°		8°	0°		8°		



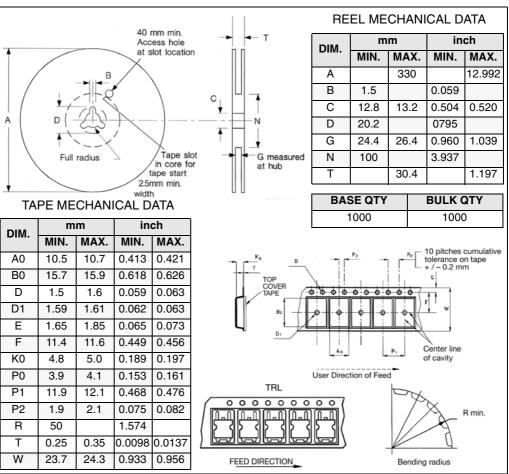


### 5 Packaging mechanical data

D<sup>2</sup>PAK FOOTPRINT



TAPE AND REEL SHIPMENT



\* on sales type



# 6 Revision history

### Table 9.Document revision history

Date	Revision	Changes
03-Mar-2008	1	First release
15-Apr-2009	2	Table 1: Device summary has been updated



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